TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

V_{CEO} , KSA708

High V_{CEO}, Complementary pair with KSA708.

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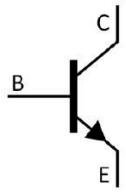
Low frequency amplifier, medium speed switching.



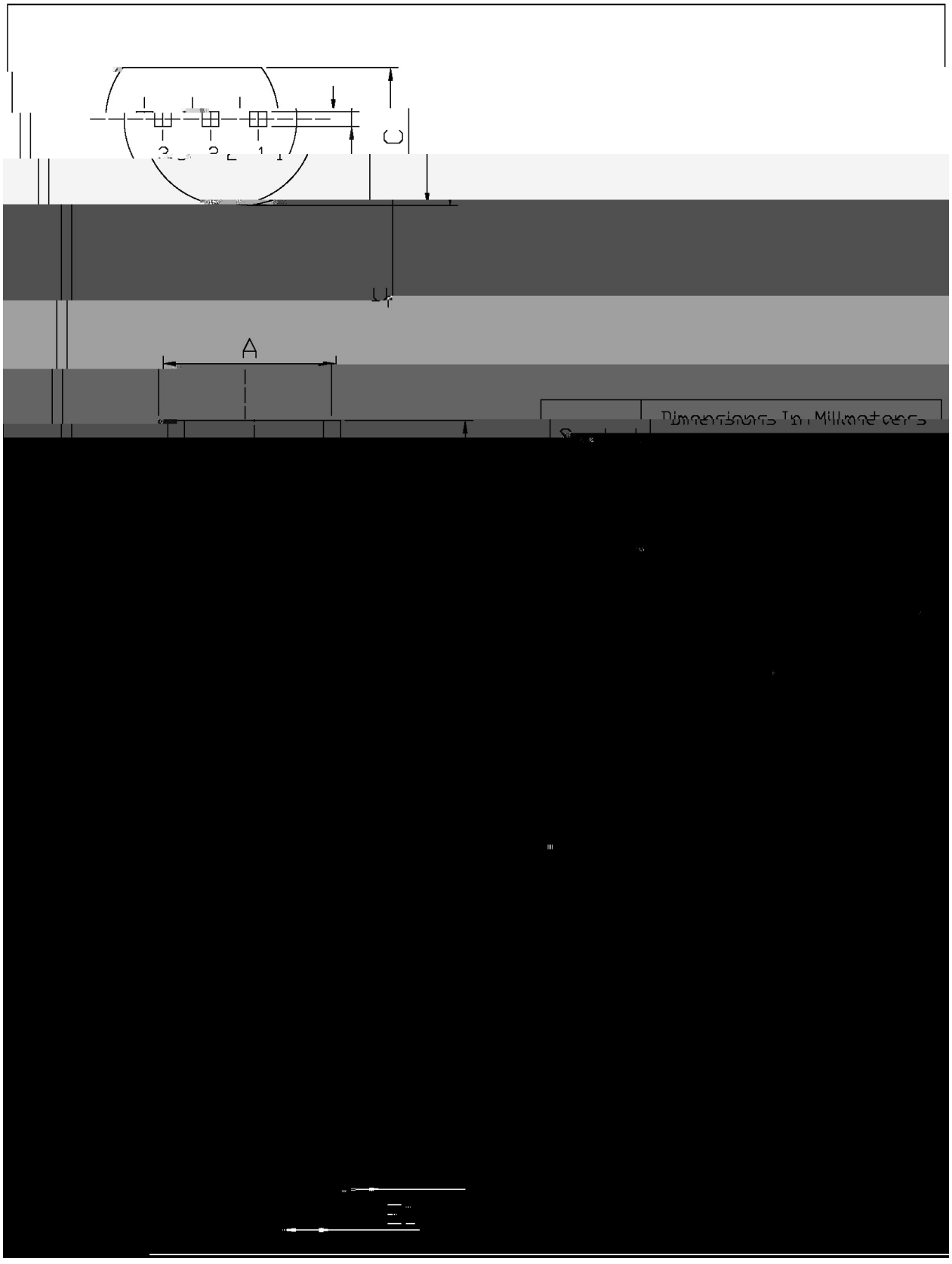
PIN1 Collector PIN 2 Base PIN 3 Emitter

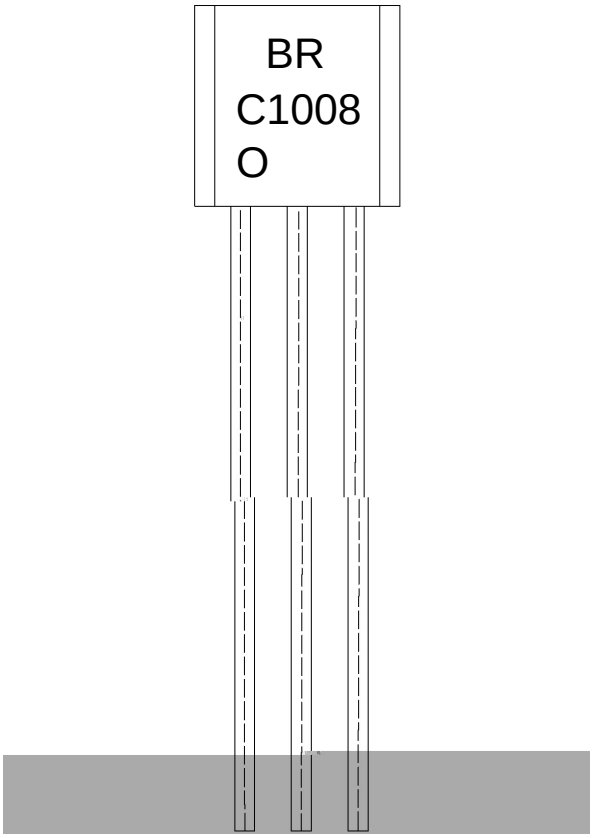
h_{FE} Classifications Symbol	R	O	Y	G
h_{FE} Range	40~80	70~140	120~240	200~400

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	8.0	V
Collector Current - Continuous	I_C	700	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-10μA I_C=0	8.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=60V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=2.0V I_C=50mA	40		400	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA I_B=50mA		0.2	0.4	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=500mA I_B=50mA		0.86	1.1	V
Transition Frequency	f_T	V_{CE}=10V I_C=50mA	30	50		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		8.0		pF

TO-92 Unit: mm





BR:

C1008

O: h_{FE}

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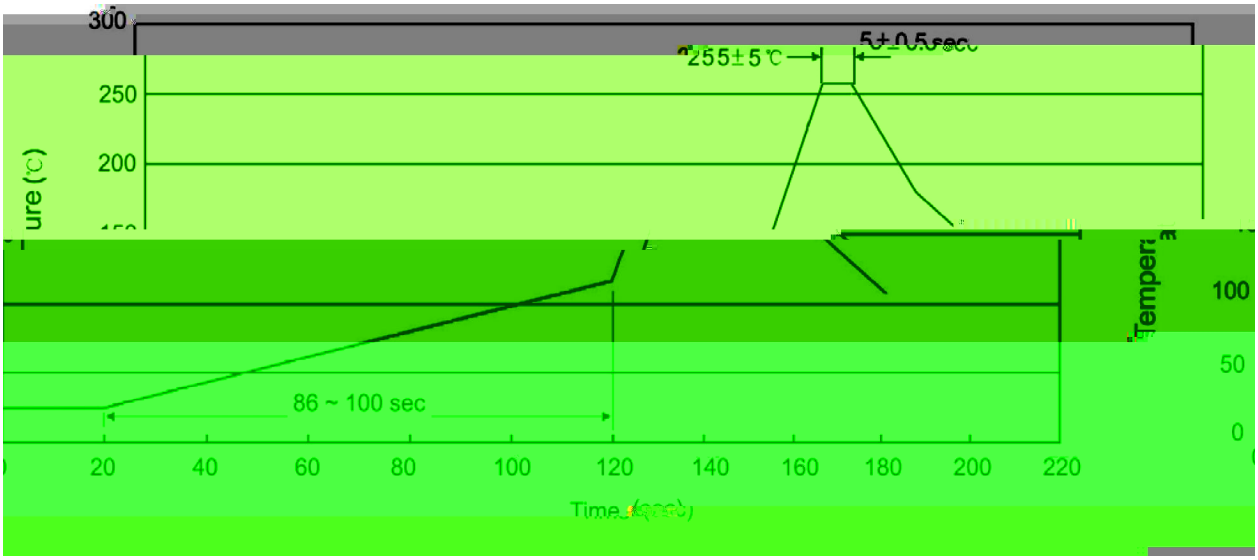
Note:

BR:	Company Code.
C1008:	Product Type.
O:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.



				Note:	
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec

/ BULK

Package Type	Units	Dimension 314	0